

Precision, Micropower, Single Supply Instrumentation Amplifier (Fixed Gain = 10 or 100)

The LT[®]1101 establishes the following milestones:

(1) It is the first micropower instrumentation amplifier,

(2) It is the first single supply instrumentation amplifier,

(3) It is the first instrumentation amplifier to feature fixed

gains of 10 and/or 100 in low cost, space-saving 8-lead

The LT1101 is completely self-contained: no external gain

setting resistor is required. The LT1101 combines its

micropower operation (75µA supply current) with a

gain error of 0.008%, gain linearity of 3ppm, gain drift of

1ppm/°C. The output is guaranteed to drive a 2k load to

Other precision specifications are also outstanding: 50µV input offset voltage, 130pA input offset current, and

low drift $(0.4\mu V/^{\circ}C \text{ and } 0.7pA/^{\circ}C)$. In addition, unlike other instrumentation amplifiers, there is no output offset

A full set of specifications are provided with ±15V dual

supplies and for single 5V supply operation. The LT1101

can be operated from a single lithium cell or two Ni-Cad

batteries. Battery voltage can drop as low as 1.8V, yet the

LT1101 still maintains its gain accuracy. In single supply

applications, both input and output voltages swing

to within a few millivolts of ground. The output sinks

current while swinging to ground—no external, power

consuming pull down resistors are needed.

±10V with excellent gain accuracy.

voltage contribution to total error.

DESCRIPTION

packages.

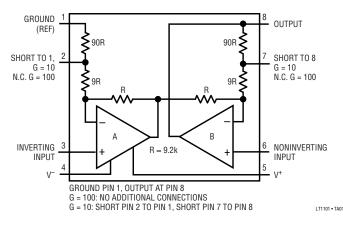
FEATURES

- Gain Error: 0.04% Max
- Gain Nonlinearity: 0.0008% (8ppm) Max
- Gain Drift: 4ppm/°C Max
- Supply Current: 105uA Max
- Offset Voltage: 160µV Max
- Offset Voltage Drift: 0.4µV/°C Typ
- Offset Current: 600pA Max
- CMRR, G = 100: 100dB Min
- 0.1Hz to 10Hz Noise: 0.9µVp-p Typ 2.3pAp-p Typ
- Gain Bandwidth Product: 250kHz Min
- Single or Dual Supply Operation
- Surface Mount Package Available

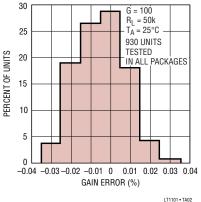
APPLICATIONS

- Differential Signal Amplification in Presence of Common Mode Voltage
- Micropower Bridge Transducer Amplifier
 - Thermocouples
 - Strain Gauges
 - Thermistors
- Differential Voltage-to-Current Converter
- Transformer Coupled Amplifier
- 4mA to 20mA Bridge Transmitter
- T, LTC and LT are registered trademarks of Linear Technology Corporation.

TYPICAL APPLICATION



Gain Error Distribution



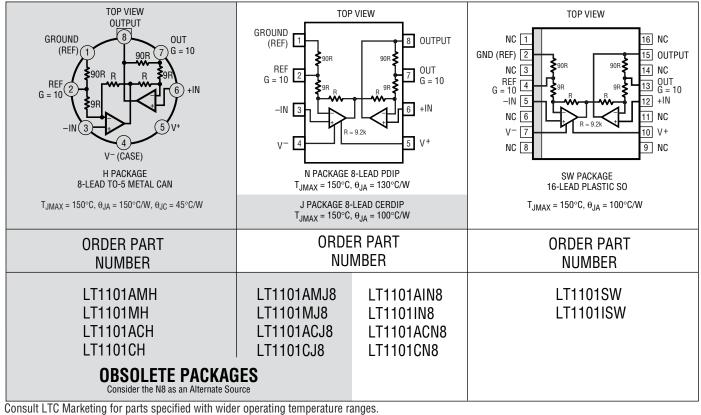


ABSOLUTE MAXIMUM RATINGS (Note 1)

Operating	Temperature	Range
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LT1101AM/LT1101M (OBSOLETE)	-55°C to 125°C
LT1101AI/LT1101I	−40°C to 85°C
LT1101AC/LT1101C	0°C to 70°C
Storage Temperature Range	-65°C to 150°C
Lead Temperature (Soldering, 10 sec)	300°C

PACKAGE/ORDER INFORMATION



ELECTRICAL CHARACTERISTICS $V_{S} = 5V$, 0V, $V_{CM} = 0.1V$, $V_{REF(PIN 1)} = 0.1V$, G = 10 or 100, $T_{A} = 25^{\circ}C$, unless

otherwise noted. (Note 4)

OVMDOL		CONDITIONO	LT1101AM/AI/AC Min typ Max			LT1101M/I/C				
SYMBOL	PARAMETER	CONDITIONS	INTIN	ITP	INIAX	MIN	ТҮР	MAX	UNITS	
G _E	Gain Error	$ \begin{array}{c} G = 100, V_0 = 0.1V \mbox{ to } 3.5V, R_L = 50k \\ G = 10, V_0 = 0.1V \mbox{ to } 3.5V, R_L = 50k \end{array} $		0.010 0009	0.050 0.040		0.011 0.010	0.075 0.060	% %	
G _{NL} G	Gain Nonlinearity	G = 100, R _L = 50k		20	60		20	75	ppm	
		G = 10, R _L = 50k (Note 2)		3	7		3	8	ppm	
V _{0S}	Input Offset Voltage			50	160		60	220	μV	
		LT1101SW					250	600	μV	
l _{os}	Input Offset Current			0.13	0.60		0.15	0.90	nA	
I _B	Input Bias Current			6	8		6	10	nA	
I _S	Supply Current			75	105		78	120	μA	
									1101fa	



ELECTRICAL CHARACTERISTICS $v_s = 5V$, ov, $v_{CM} = 0.1V$, $v_{REF(PIN 1)} = 0.1V$, G = 10 or 100, $T_A = 25^{\circ}C$, unless otherwise noted. (Note 4)

			LT1	101AM/A	I/AC	L			
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	ТҮР	MAX	UNITS
CMRR	Common Mode Rejection Ratio	$\begin{array}{l} \mbox{1k Source Imbalance} \\ \mbox{G} = 100, \ \mbox{V}_{CM} = 0.07 \mbox{V to } 3.4 \mbox{V} \\ \mbox{G} = 10, \ \mbox{V}_{CM} = 0.07 \mbox{V to } 3.1 \mbox{V} \end{array}$	95 84	106 100		92 82	105 99		dB dB
	Minimum Supply Voltage	(Note 5)		1.8	2.3		1.8	2.3	V
V ₀	Maximum Output Voltage Swing	Output High, 50k to GND Output High, 2k to GND Output Low, $V_{REF} = 0$, No Load Output Low, $V_{REF} = 0$, 2k to GND Output Low, $V_{REF} = 0$, $I_{SINK} = 100 \mu A$	4.1 3.5	4.3 3.9 3.3 0.5 90	6 1 130	4.1 3.5	4.3 3.9 3.3 0.5 90	6 1 130	V V mV mV mV
BW	Bandwidth	G = 100 (Note 2) G = 10 (Note 2)	2.0 22	3.0 33		2.0 22	3.0 33		kHz kHz
SR	Slew Rate	(Note 2)	0.04	0.07		0.04	0.07		V/µs

V_S = $\pm 15V,~V_{CM}$ = 0V, T_A = 25°C, Gain = 10 or 100, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	LT ⁻ Min	1101AM/A Typ	I/AC Max	I Min	_T1101M/I/ TYP	'C Max	UNITS
GE	Gain Error	$ \begin{array}{c} G = 100, V_0 = \pm 10V, R_L = 50k \\ G = 100, V_0 = \pm 10V, R_L = 2k \\ G = 100, V_0 = \pm 10V, R_L = 50k \text{ or } 2k \end{array} $		0.008 0.011 0.008	0.040 0.055 0.040		0.009 0.012 0.009	0.060 0.070 0.060	% % %
G _{NL}	Gain Nonlinearity			7 24 3	16 45 8		8 25 3	20 60 9	ppm ppm ppm
V _{OS}	Input Offset Voltage	LT1101SW		50	160		60 250	220 600	μV μV
l _{OS}	Input Offset Current			0.13	0.60		0.15	0.90	nA
I _B	Input Bias Current			6	8		6	10	nA
	Input Resistance Common Mode Differential Mode	(Note 2) (Note 2)	4 7	7 12		3 5	7 12		GΩ GΩ
e _n	Input Noise Voltage	0.1Hz to 10Hz (Note 3)		0.9	1.8		0.9		µVр-р
	Input Noise Voltage Density	f ₀ = 10Hz (Note 3) f ₀ = 1000Hz (Note 3)		45 43	64 54		45 43		nV/√ <u>Hz</u> nV/√Hz
i _n	Input Noise Current	0.1Hz to 10Hz (Note 3)		2.3	4.0		2.3		рАр-р
	Input Noise Current Density	f ₀ =10Hz (Note 3) f ₀ = 1000Hz		0.06 0.02	0.10		0.06 0.02		pA/√ <u>Hz</u> pA/√Hz
	Input Voltage Range	G = 100 G = 10	13.0 -14.4 11.5 -13.0	13.8 14.7 12.5 13.3		13.0 -14.4 11.5 -13.0	13.8 -14.7 12.5 -13.3		V V V V
CMRR	Common Mode Rejection Ratio	1k Source Imbalance G = 100, Over CM Range G = 10, Over CM Range	100 84	112 100		98 82	112 99		dB dB
PSRR	Power Supply Rejection Ratio	$V_{\rm S}$ = +2.2V, -0.1V to ±18V	102	114		100	114		dB
Is	Supply Current			92	130		94	150	μA
	1	1	1			1			1101fa



ELECTRICAL CHARACTERISTICS $V_{S} = \pm 15V$, $V_{CM} = 0V$, $T_{A} = 25^{\circ}C$, Gain = 10 or 100, unless otherwise noted.

			LT1101AM/AI			LT1101M/I			
SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
V ₀	Maximum Output Voltage Swing	$R_{L} = 50k$ $R_{L} = 2k$	13.0 11.0	14.2 13.2		13.0 11.0	14.2 13.2		V V
BW	Bandwidth	G = 100 (Note 2) G = 10 (Note 2)	2.3 25	3.5 37		2.3 25	3.5 37		kHz kHz
SR	Slew Rate		0.06	0.10		0.06	0.10		V/µs

ELECTRICAL CHARACTERISTICS $V_S = \pm 15V$, $V_{CM} = 0V$, Gain = 10 or 100, $-55^{\circ}C \le T_A \le 125^{\circ}C$ for AM/M grades, $-40^{\circ}C \le T_A \le 85^{\circ}C$ for Al/l grades, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	L Min	.T1101AM/ Typ	AI Max	MIN	LT1101M/I TYP	MAX	UNITS
G _E	Gain Error	$ \begin{array}{l} G = 100, \ V_0 = \pm 10V, \ R_L = 50k \\ G = 100, \ V_0 = \pm 10V, \ R_L = 5k \\ G = 10, \ V_0 = \pm 10V, \ R_L = 50k \ or \ 5k \end{array} $		0.024 0.030 0.015	0.070 0.100 0.070		0.026 0.035 0.018	0.100 0.130 0.100	% % %
TCG _E	Gain Error Drift (Note 2)			2 2 1	4 7 4		2 2 1	5 8 5	ppm/°C ppm/°C ppm/°C
G _{NL}	Gain Nonlinearity			24 70 4 10	70 300 13 40		26 75 5 12	90 500 15 60	ppm ppm ppm ppm
V _{OS}	Input Offset Voltage	LT1101ISW		90	350		110 110	500 950	μV μV
$\Delta V_{0S}/\Delta T$	Input Offset Voltage Drift	(Note 2) LT1101ISW		0.4	2.0		0.5 0.5	2.8 4.8	μV/°C mV/°C
I _{OS}	Input Offset Current			0.16	0.80		0.19	1.30	nA
$\Delta I_{0S} / \Delta T$	Input Offset Current Drift	(Note 2)		0.5	4.0		0.8	7.0	pA/°C
I _B	Input Bias Current			7	10		7	12	nA
$\Delta I_{B} / \Delta T$	Input Bias Current Drift	(Note 2)		10	25		10	30	pA/°C
CMRR	Common Mode Rejection Ratio	$ G = 100, V_{CM} = -14.4V \text{ to } 13V \\ G = 100, V_{CM} = -13V \text{ to } 11.5V $	96 80	111 99		94 78	111 98		dB dB
PSRR	Power Supply Rejection Ratio	$V_{\rm S} = 3.0, -0.1 V \text{ to } \pm 18 V$	98	110		94	110		dB
I _S	Supply Current			105	165		108	190	μA
V ₀	Maximum Output Voltage Swing	$R_{L} = 50k$ $R_{L} = 5k$	12.5 11.0	14.0 13.5		12.5 11.0	14.0 13.5		V V



ELECTRICAL CHARACTERISTICS $V_S = \pm 15V$, $V_{CM} = 0V$, Gain = 10 or 100, $0^{\circ}C \le T_A \le 70^{\circ}C$, unless otherwise noted.

				LT1101AC			LT1101C/S		
SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
G _E	Gain Error	$ \begin{array}{l} G = 100, V_0 = \pm 10V, R_L = 50k \\ G = 100, V_0 = \pm 10V, R_L = 2k \\ G = 10, V_0 = \pm 10V, R_L = 50k \text{ or } 2k \end{array} $		0.012 0.018 0.009	0.055 0.085 0.055		0.014 0.020 0.010	0.080 0.100 0.080	% % %
TCG _E	Gain Error Drift (Note 2)			1 2 1	4 7 4		1 2 1	5 9 5	ppm/°C ppm/°C ppm/°C
G _{NL}	Gain Nonlinearity			9 33 4	25 75 10		10 36 4	35 100 11	ppm ppm ppm
V _{OS}	Input Offset Voltage	LT1101SW		70	250		85 300	350 800	μV μV
$\Delta V_{0S} / \Delta T$	Input Offset Voltage Drift	(Note 2) LT1101SW		0.4	2.0		0.5 1.2	2.8 4.5	μV/°C μV/°C
I _{OS}	Input Offset Current			0.14	0.70		0.17	1.10	nA
$\Delta I_{0S} / \Delta T$	Input Offset Current Drift	(Note 2)		0.5	4.0		0.8	7.0	pA/°C
IB	Input Bias Current			6	9		6	11	nA
$\Delta I_{\rm B} / \Delta T$	Input Bias Current Drift	(Note 2)		10	25		10	30	pA/°C
CMRR	Common Mode Rejection Ratio		98 82	112 100		96 80	112 99		dB dB
PSRR	Power Supply Rejection Ratio	$V_{\rm S}$ = 2.5, -0.1V to ±18V	100	112		97	112		dB
I _S	Supply Current			98	148		100	170	μA
V ₀	Maximum Output Voltage Swing	$R_{L} = 50k$ $R_{L} = 2k$	±12.5 ±10.5	±14.1 ±13.0		±12.5 ±10.5	±14.1 ±13.0		V V



$\begin{array}{l} \textbf{ELECTRICAL CHARACTERISTICS} \\ V_S = 5V, \ 0V, \ V_{CM} = 0.1V, \ V_{REF(PIN \ 1)} = 0.1V, \ Gain = 10 \ or \ 100, \\ -40^\circ C \leq T_A \leq 85^\circ C \ for \ Al/l \ grades, \ unless \ otherwise \ noted \ (Note \ 4). \end{array}$

			L	T1101AM/	AI		LT1101M/I		
SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
G _E	Gain Error	$ \begin{array}{l} G = 100, V_0 = 0.1V \mbox{ to } 3.5V, R_L = 50k \\ G = 10, V_{CM} = 0.15, R_L = 50k \end{array} $		0.026 0.011	0.080 0.070		0.028 0.014	0.120 0.100	% %
TCG _E	Gain Error Drift	R _L = 50k (Note 2)		1	4		1	5	ppm/°C
G _{NL}	Gain Nonlinearity			45 4	110 13		48 5	140 15	ppm ppm
V _{OS}	Input Offset Voltage	LT1101ISW		90	350		110 110	500 950	μV μV
$\Delta V_{0S} / \Delta T$	Input Offset Voltage Drift	(Note 2) LT1101ISW		0.4	2.0		0.5 0.5	2.8 4.8	μV/°C μV/°C
l _{OS}	Input Offset Current			0.16	0.80		0.19	1.30	nA
$\Delta V_{0S} / \Delta T$	Input Offset Current Drift	(Note 2)		0.5	4.0		0.8	7.0	pA/°C
IB	Input Bias Current			7	10		7	12	nA
$\Delta I_{B} / \Delta T$	Input Bias Current Drift	(Note 2)		10	25		10	30	pA/°C
CMRR	Common Mode Rejection Ratio	$ \begin{array}{l} G = 100, V_{CM} = 0.1V \mbox{ to } 3.2V \\ G = 10, V_{CM} = 0.1V \mbox{ to } 2.9V, V_{REF} = 0.15V \\ \end{array} $	91 80	105 98		88 77	104 97		dB dB
I _S	Supply Current			88	135		92	160	μΑ
V ₀	Maximum Output Voltage Swing	Output High, 50k to GND Output High, 2k to GND Output Low, $V_{REF} = 0$, No Load Output Low, $V_{REF} = 0$, 2k to GND Output Low, $V_{REF} = 0$, $I_{SINK} = 100\mu$ A	3.8 3.0	4.1 3.7 4.5 0.7 125	8 1.5 170	3.8 3.0	4.1 3.7 4.5 0.7 125	8 1.5 170	V V mV mV WV



ELECTRICAL CHARACTERISTICS $V_S = 5V$, 0V, $V_{CM} = 0.1V$, $V_{REF(PIN 1)} = 0.1V$, Gain = 10 or 100, $0^{\circ}C \le T_A \le 70^{\circ}C$, unless otherwise noted (Note 4).

RAMETER n Error	CONDITIONS G = 100, V ₀ = 0.1V to 3.5V, R _L = 50k	MIN	ТҮР	MAX		, -	1	
	G = 100, V_0 = 0.1V to 3.5V, R_L = 50k			IWIAA	MIN	ТҮР	MAX	UNITS
	$G = 10, V_{CM} = 0.15V, R_L = 50k$		0.017 0.010	0.065 0.060		0.018 0.012	0.095 0.080	% %
n Error Drift	R _L = 50k (Note 2)		1	4		1	5	ppm/°C
n Nonlinearity	$G = 100, R_L = 50k$ $G = 10, R_L = 50k$ (Note 2)		25 4	80 10		25 4	100 11	ppm ppm
ut Offset Voltage	LT1101SW		70	250		85 300	350 800	μV μV
ut Offset Voltage Drift	(Note 2) LT1101SW		0.4	2.0		0.5 1.2	2.8 4.5	μV/°C μV/°C
ut Offset Current			0.14	0.70		0.17	1.10	nA
ut Offset Current Drift	(Note 2)		0.5	4.0		0.8	7	pA/°C
ut Bias Current			6	9		6	11	nA
ut Bias Current Drift	(Note 2)		10	25		10	30	pA/°C
mmon Mode ection Ratio	$ \begin{array}{l} G = 100, V_{CM} = 0.07V \ to \ 3.3V \\ G = 10, V_{CM} = 0.07V \ to \ 3V, V_{REF} = 0.15V \end{array} $	93 82	105 99		90 80	104 98		dB dB
oply Current			80	120		85	145	μA
ximum Output tage Swing	Output High, 50k to GND Output High, 2k to GND Output Low, $V_{REF} = 0$, No Load Output Low, $V_{REF} = 0$, 2k to GND	4.0 3.3	4.2 3.8 4 0.6	7 1.2	4.0 3.3	4.2 3.8 4 0.6	7 1.2	V V mV mV
xim	um Output	um Output Output High, 50k to GND 9 Swing Output High, 2k to GND Output Low, V _{REF} = 0, No Load	um Output e Swing Output High, 50k to GND Output High, 2k to GND Output Low, V _{REF} = 0, No Load Output Low, V _{REF} = 0, 2k to GND	um OutputOutput High, 50k to GND4.04.2 \diamond SwingOutput High, 2k to GND3.33.8Output Low, V _{REF} = 0, No Load44Output Low, V _{REF} = 0, 2k to GND0.6	um OutputOutput High, 50k to GND4.04.2 \diamond SwingOutput High, 2k to GND3.33.8Output Low, V _{REF} = 0, No Load47Output Low, V _{REF} = 0, 2k to GND0.61.2	um OutputOutput High, 50k to GND 4.0 4.2 4.0 \circ SwingOutput High, 2k to GND 3.3 3.8 3.3 Output Low, V _{REF} = 0, No Load 4 7 Output Low, V _{REF} = 0, 2k to GND 0.6 1.2	um Output Output High, 50k to GND 4.0 4.2 4.0 4.2 9 Swing Output High, 2k to GND 3.3 3.8 3.3 3.8 0 utput Low, V _{REF} = 0, No Load 4 7 4 0 utput Low, V _{REF} = 0, 2k to GND 0.6 1.2 0.6	um Output Output High, 50k to GND 4.0 4.2 4.0 4.2 9 Swing Output High, 2k to GND 3.3 3.8 3.3 3.8 Output Low, V _{REF} = 0, No Load 4 7 4 7 Output Low, V _{REF} = 0, 2k to GND 0.6 1.2 0.6 1.2

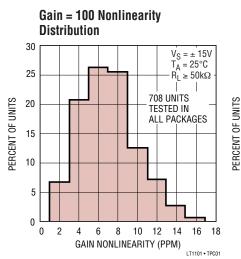
Note 1: Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

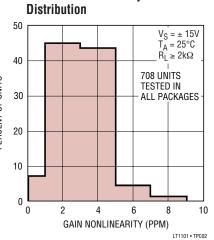
Note 2: This parameter is not tested. It is guaranteed by design and by inference from other tests.

Note 3: This parameter is tested on a sample basis only.

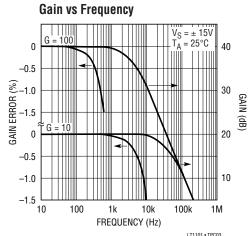
Note 4: These test conditions are equivalent to $V_S = 4.9V, -0.1V$, $V_{CM} = 0V, V_{REF(PIN1)} = 0V.$

Note 5: Minimum supply voltage is guaranteed by the power supply rejection test. The LT1101 actually works at 1.8V supply with minimal degradation in performance.

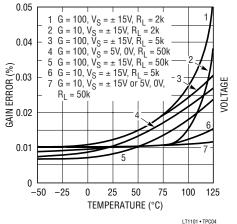




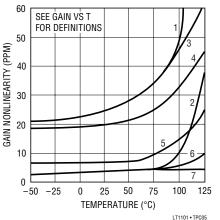
Gain = 10 Nonlinearity



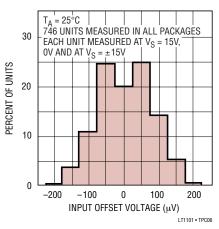
Gain Error Over Temperature

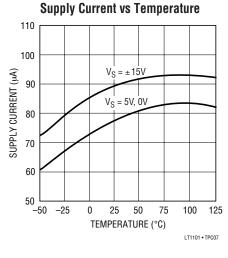


Gain Nonlinearity Temperature

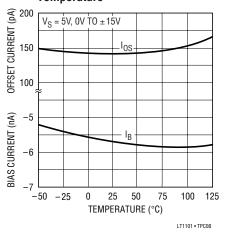


Input Offset Voltage Distribution

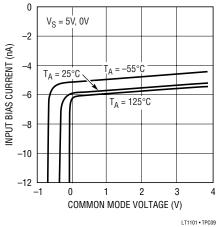




Input Bias and Offset Currents vs Temperature

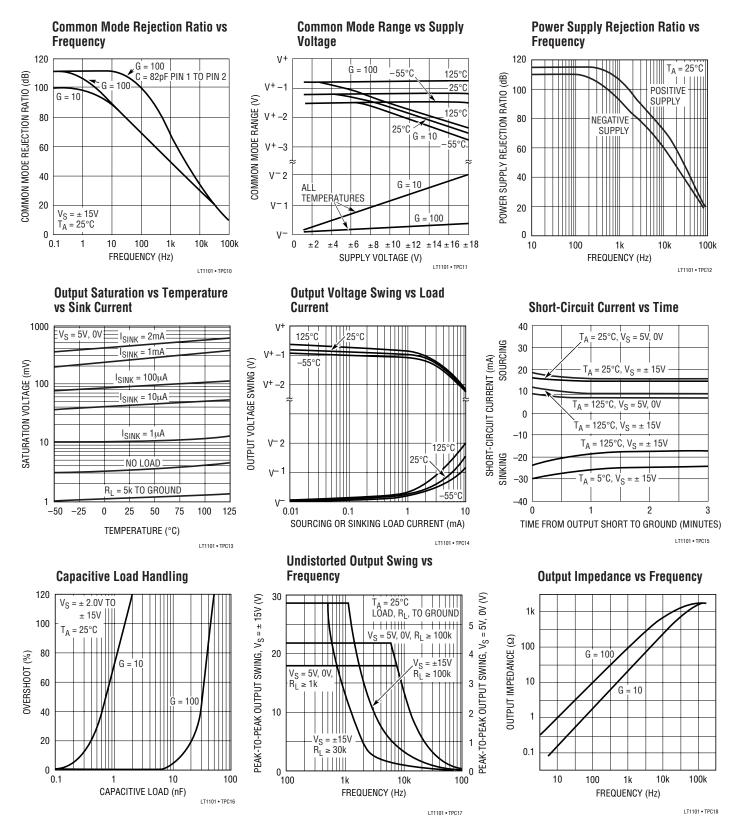


Input Bias Current vs Common Mode Voltage

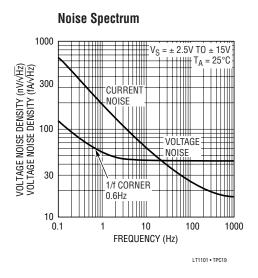


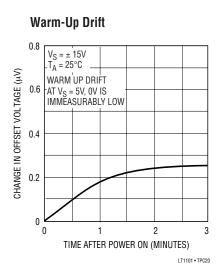
1101 • TPC09



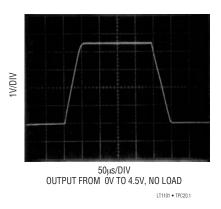


1 T1101 • TPC18

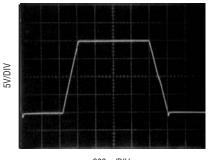




Large Signal Transient Response $G = 10, V_S = 5V, 0V$



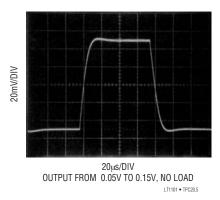
Large Signal Transient Response $G = 10, V_S = 15V$



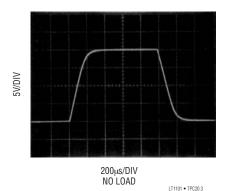
200µs/DIV NO LOAD

LT1101 • TPC20.2

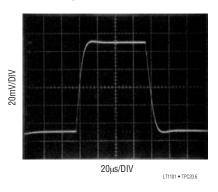




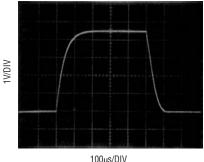
Large Signal Transient Response G = 100, V_S = $\pm 15V$



Small Signal Transient Response $G = 10, V_S = \pm 15V$

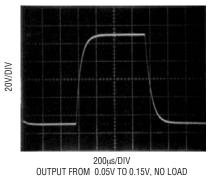


Large Signal Transient Response G = 100, V_S = 5V, 0V



100µs/DIV OUTPUT FROM OV TO 4.5V, NO LOAD

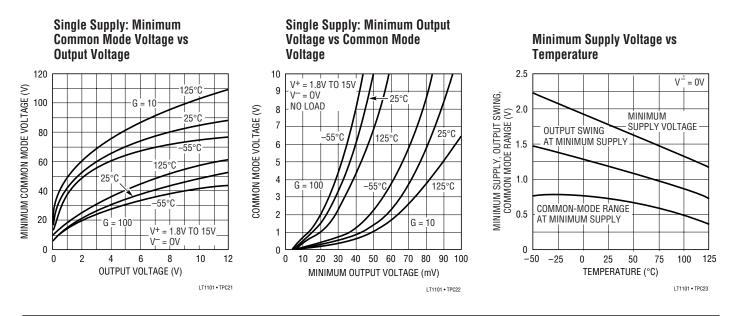
Small Signal Transient Response G = 100, V_S = 5V, 0V



(RESPONSE WITH $V_S = \pm 15V$, G = 100 IS IDENTICAL)

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APPLICATIONS INFORMATION

Single Supply Applications

The LT1101 is the first instrumentation amplifier which is fully specified for single supply operation, (i.e. when the negative supply is 0V). Both the input common mode range and the output swing are within a few millivolts of ground.

Probably the most common application for instrumentation amplifiers is amplifying a differential signal from a transducer or sensor resistance bridge. All competitive instrumentation amplifiers have a minimum required common mode voltage which is 3V to 5V above the negative supply. This means that the voltage across the bridge has to be 6V to 10V or dual supplies have to be used (i.e., micropower) single battery usage is not attainable on competitive devices.

The minimum output voltage obtainable on the LT1101 is a function of the input common mode voltage. When the common mode voltage is high and the output is low, current will flow from the output of amplifier A into the output of amplifier B. See the Minimum Output Voltage vs Common Mode Voltage plot.

Similarly, the Single Supply Minimum Common Mode Voltage vs Output Voltage plot specifies the expected common mode range.

When the output is high and input common mode is low, the output of amplifier A has to sink current coming from the output of amplifier B. Since amplifier A is effectively in unity gain, its input is limited by its output.

Common Mode Rejection vs Frequency

The common mode rejection ratio (CMRR) of the LT1101 starts to roll off at a relatively low frequency. However, as shown on the Common Mode Rejection Ratio vs Frequency plot, CMRR can be enhanced significantly by connecting an 82pF capacitor between pins 1 and 2. This improvement is only available in the gain 100 configuration, and it is in excess of 30dB at 60Hz.

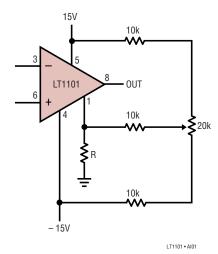
Offset Nulling

The LT1101 is not equipped with dedicated offset null terminals. In many bridge transducer or sensor applications, calibrating the bridge simultaneously eliminates the instrumentation amplifier's offset as a source of error. For example, in the Micropower Remote Temperature Sensor Application shown, one adjustment removes the offset errors due to the temperature sensor, voltage reference and the LT1101.

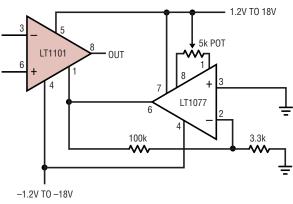


APPLICATIONS INFORMATION

A simple resistive offset adjust procedure is shown below. If $R = 5\Omega$ for G = 10, and $R = 50\Omega$ for G = 100, then the effect of R on gain error is approximately 0.006%. Unfortunately, about 450μ A has to flow through R to bias the reference terminal (Pin 1) and to null out the worst-case offset voltage. The total current through the resistor network can exceed 1mA, and the micropower advantage of the LT1101 is lost.



Another offset adjust scheme uses the LT1077 micropower op amp to drive the reference Pin 1. Gain error and common mode rejection are unaffected, the total current increase is 45μ A. The offset of the LT1077 is trimmed and amplified to match and cancel the offset voltage of the LT1101. Output offset null range is ±25mV.



LT1101 • AI02

Gains Between 10 and 100

Gains between 10 and 100 can be achieved by connecting two equal resistors (= R_x) between Pins 1 and 2 and Pins 7 and 8.

$$Gain = 10 + \frac{R_x}{R + R_x/90}$$

The nominal value of R is $9.2k\Omega$. The usefulness of this method is limited by the fact that R is not controlled to better than $\pm 10\%$ absolute accuracy in production. However, on any specific unit, 90R can be measured between Pins 1 and 2.

Input Protection

Instrumentation amplifiers are often used in harsh environments where overload conditions can occur. The LT1101 employs PNP input transistors, consequently the differential input voltage can be $\pm 30V$ (with $\pm 15V$ supplies, $\pm 36V$ with $\pm 18V$ supplies) without an increase in input bias current. Competitive instrumentation amplifiers have NPN inputs which are protected by back-to-back diodes. When the differential input voltage exceeds $\pm 1.3V$ on these competitive devices, input current increases to the milliampere level; more than $\pm 10V$ differential voltage can cause permanent damage.

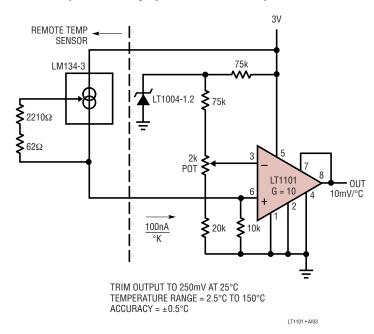
When the LT1101's inputs are pulled above the positive supply, the inputs will clamp a diode voltage above the positive supply. No damage will occur if the input current is limited to 20mA.

 500Ω resistors in series with the inputs protect the LT1101 when the inputs are pulled as much as 10V below the negative supply.

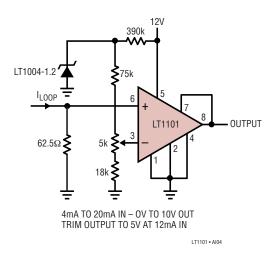


APPLICATIONS INFORMATION

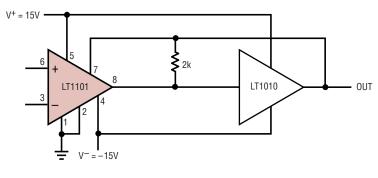
Micropower, Battery Operated Remote Temperature Sensor



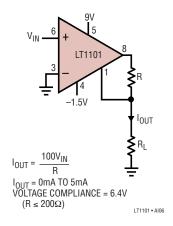
4mA to 20mA Loop Receiver



Instrumentation Amplifier with ± 150 mA Output Current

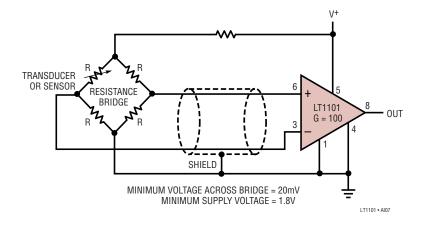


 Voltage Controlled Current Source



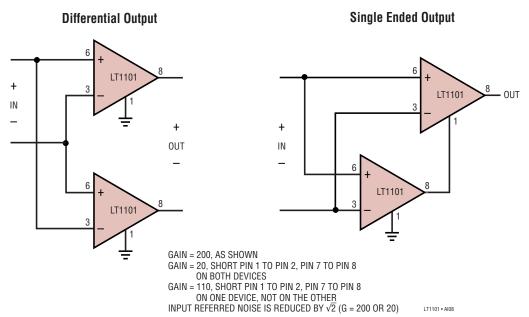


APPLICATIONS INFORMATION



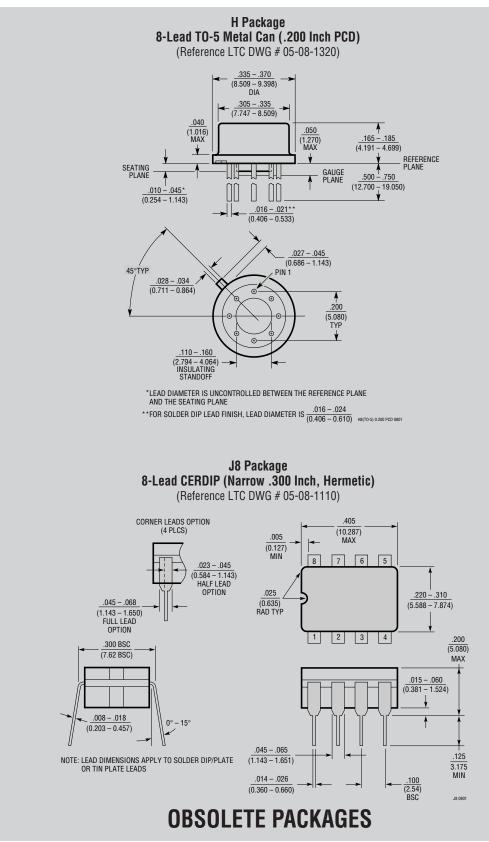
Differential Voltage Amplification from a Resistance Bridge







PACKAGE DESCRIPTION





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